International
IOR Rectifier

IRF7842PbF

HEXFET® Power MOSFET

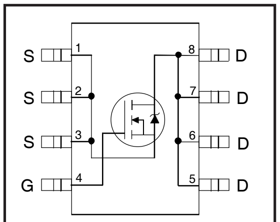
Applications

- Synchronous MOSFET for Notebook Processor Power
- Secondary Synchronous Rectification for Isolated DC-DC Converters
- Synchronous Fet for Non-Isolated DC-DC Converters
- Lead-Free

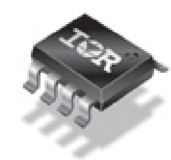
V_{DSS}	$R_{DS(on)}$ max	Qg (typ.)
40V	5.0mΩ@V_{GS} = 10V	33nC

Benefits

- Very Low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current



Top View


SO-8

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7842PbF	SO-8	Tube/Bulk	95	IRF7842PbF
		Tape and Reel	4000	IRF7842TRPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	18	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	14	
I_{DM}	Pulsed Drain Current ①	140	
P_D @T_A = 25°C	Power Dissipation ④	2.5	W
P_D @T_A = 70°C	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	——	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④⑤	——	50	

Notes ① through ⑤ are on page 10

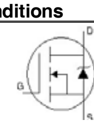
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.037	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	4.0	5.0	mΩ	V_{GS} = 10V, I_D = 17A ③
		—	4.7	5.9		V_{GS} = 4.5V, I_D = 14A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	—	2.25	V	V_{DS} = V_{GS}, I_D = 250µA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	- 5.6	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	µA	V_{DS} = 32V, V_{GS} = 0V
		—	—	150		V_{DS} = 32V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
gfs	Forward Transconductance	81	—	—	S	V_{DS} = 20V, I_D = 14A
Q_g	Total Gate Charge	—	33	50		
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	9.6	—		V_{DS} = 20V
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	2.8	—	nC	V_{GS} = 4.5V
Q_{gd}	Gate-to-Drain Charge	—	10	—		I_D = 14A
Q_{godr}	Gate Charge Overdrive	—	10.6	—		
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	—	12.8	—		
Q_{oss}	Output Charge	—	18	—	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	—	1.3	2.6	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	14	—		V_{DD} = 20V, V_{GS} = 4.5V ③
t_r	Rise Time	—	12	—		I_D = 14A
$t_{d(off)}$	Turn-Off Delay Time	—	21	—	ns	Clamped Inductive Load
t_f	Fall Time	—	5.0	—		
C_{iss}	Input Capacitance	—	4500	—		V_{GS} = 0V
C_{oss}	Output Capacitance	—	680	—	pF	V_{DS} = 20V
C_{rss}	Reverse Transfer Capacitance	—	310	—		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	50	mJ
I_{AR}	Avalanche Current ①	—	14	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	140		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	T_J = 25°C, I_S = 14A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	99	150	ns	T_J = 25°C, I_F = 14A, V_{DD} = 20V
Q_{rr}	Reverse Recovery Charge	—	11	17	nC	di/dt = 100A/µs ③

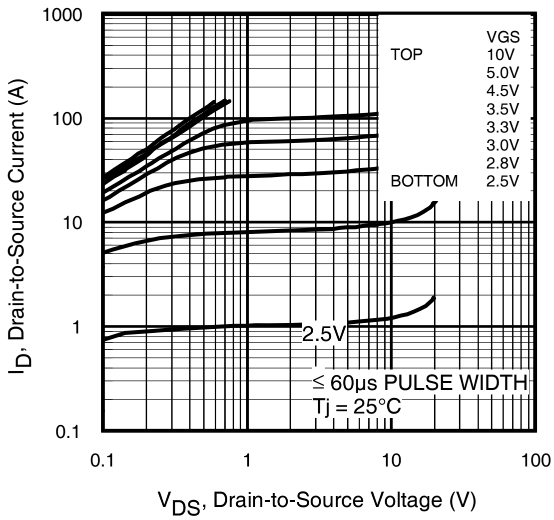


Fig 1. Typical Output Characteristics

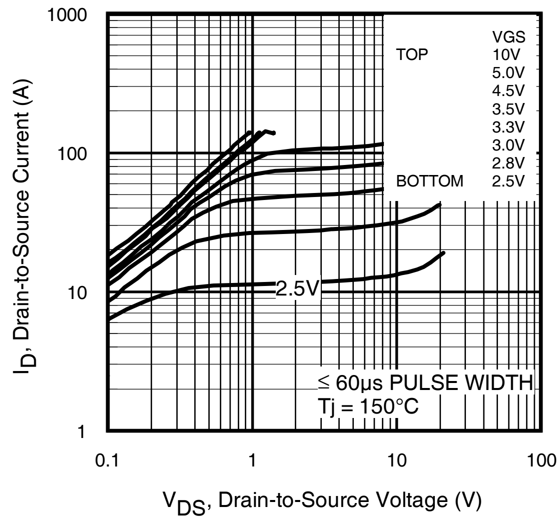


Fig 2. Typical Output Characteristics

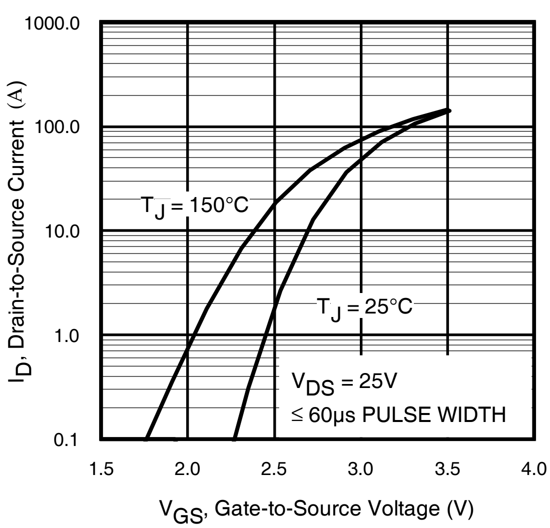


Fig 3. Typical Transfer Characteristics

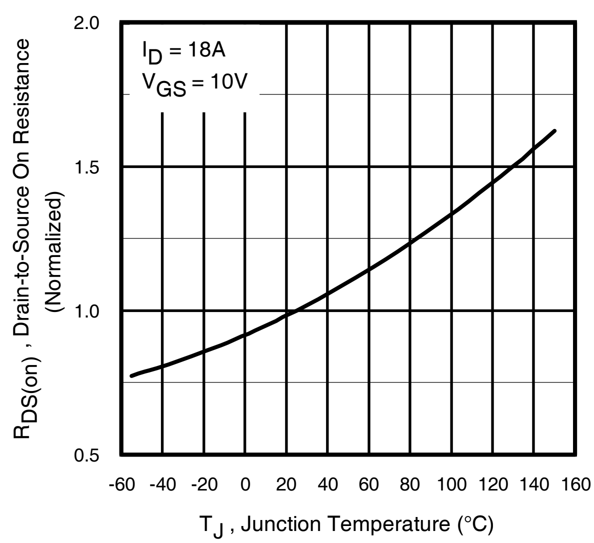


Fig 4. Normalized On-Resistance
Vs. Temperature

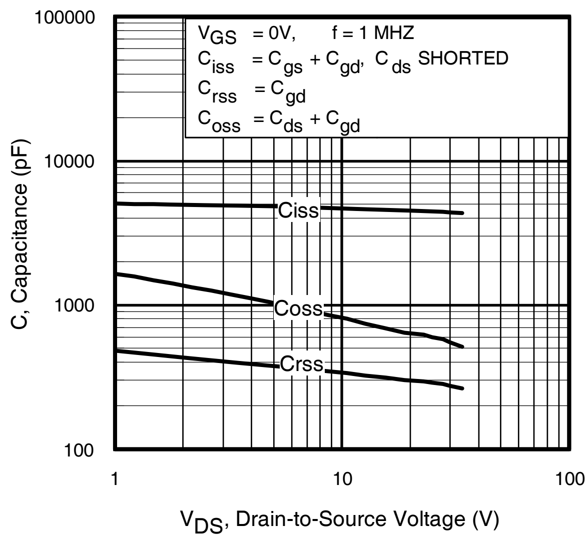


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

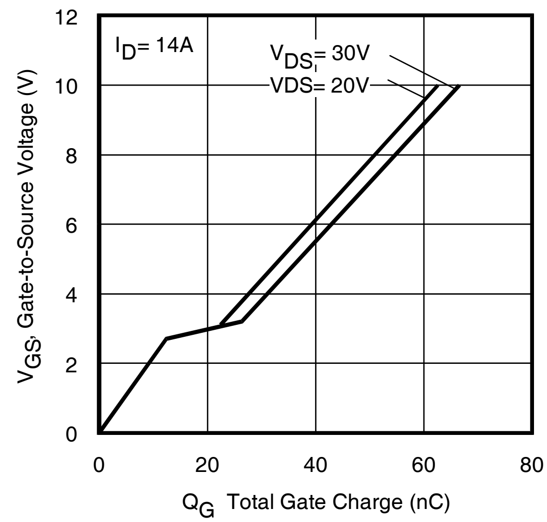


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

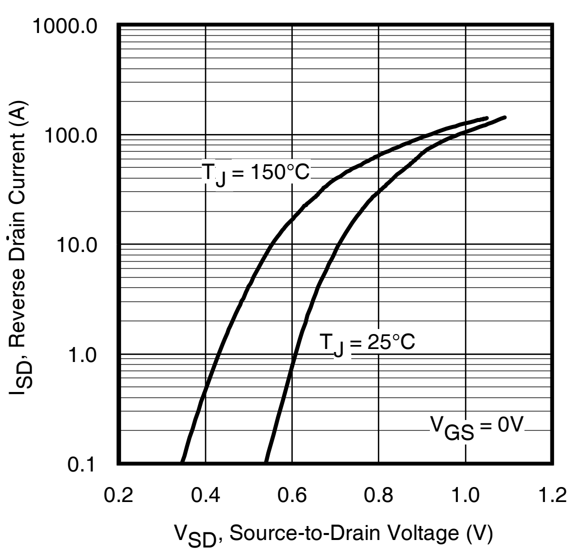


Fig 7. Typical Source-Drain Diode Forward Voltage

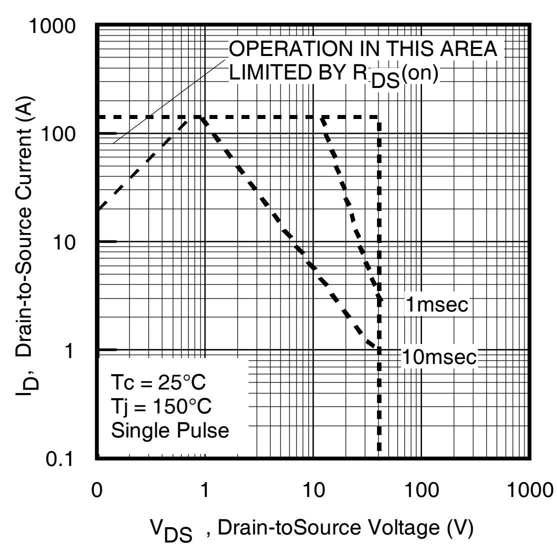


Fig 8. Maximum Safe Operating Area

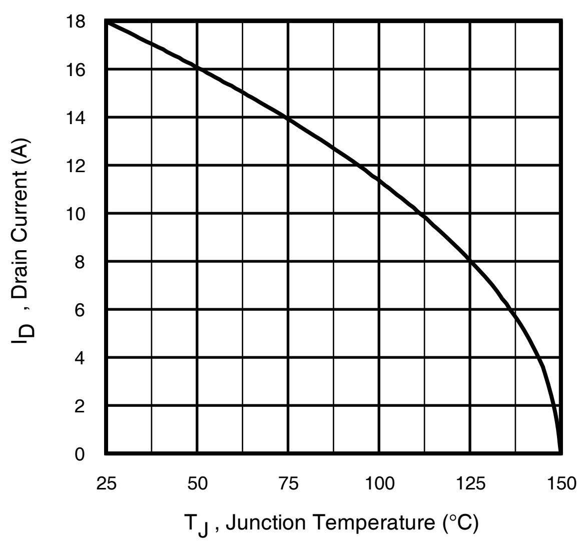


Fig 9. Maximum Drain Current Vs. Case Temperature

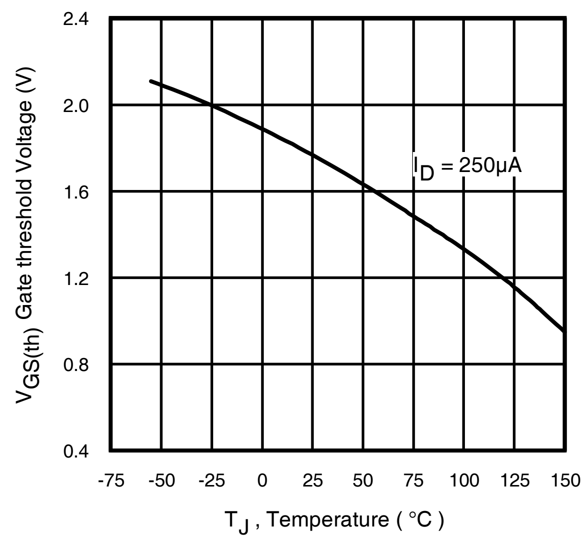


Fig 10. Threshold Voltage Vs. Temperature

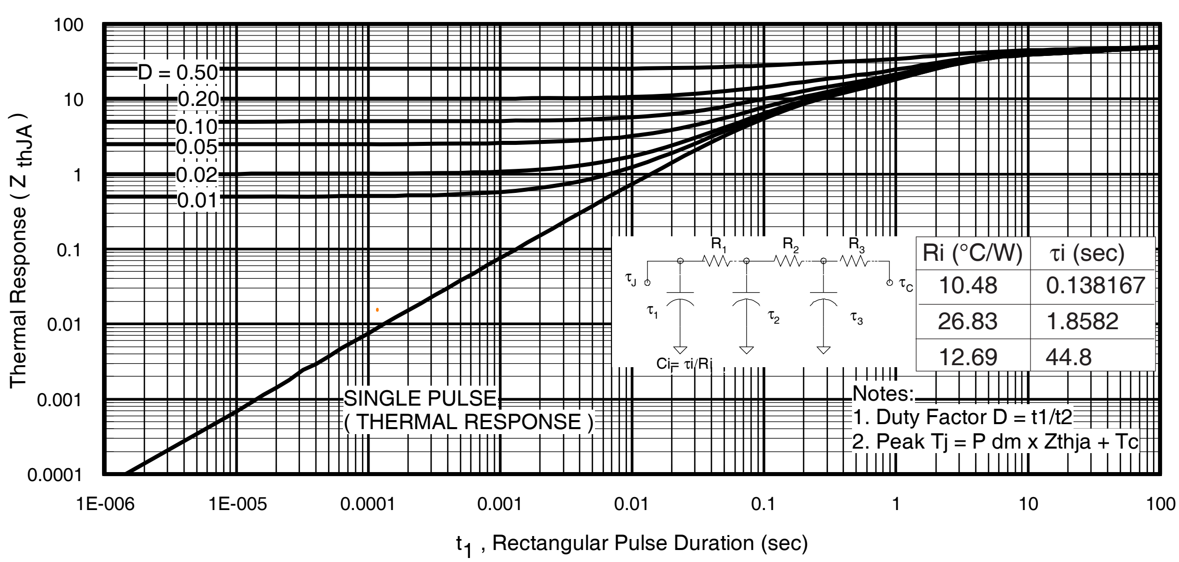


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

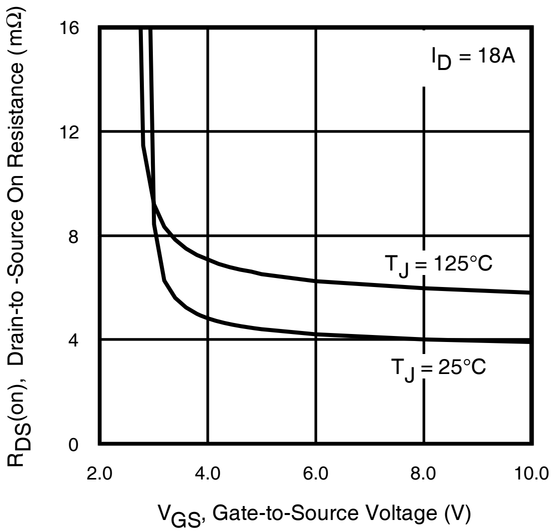


Fig 12. On-Resistance Vs. Gate Voltage

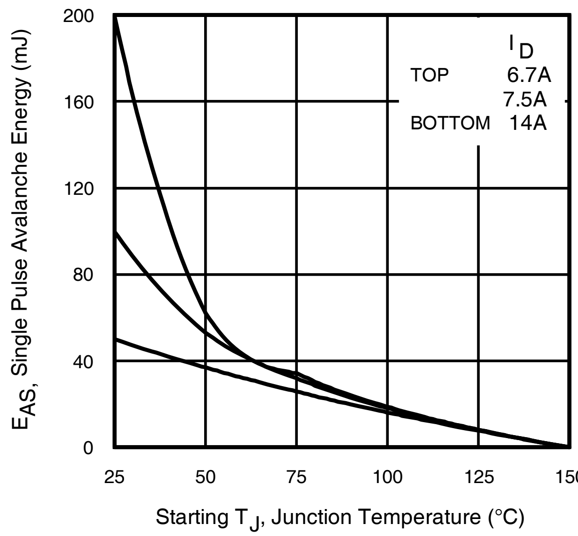


Fig 13c. Maximum Avalanche Energy Vs. Drain Current

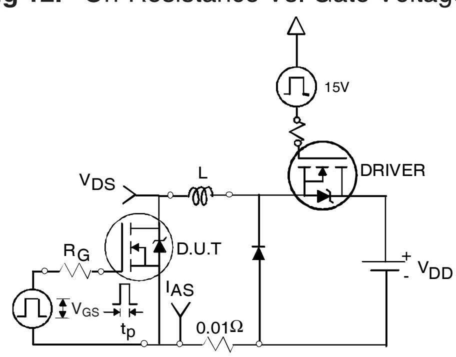


Fig 13a. Unclamped Inductive Test Circuit

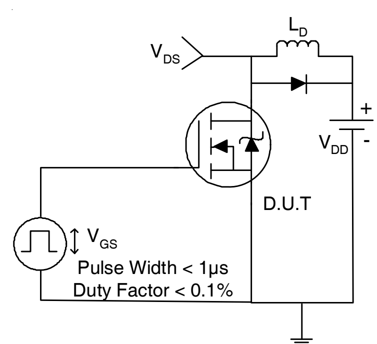


Fig 14a. Switching Time Test Circuit

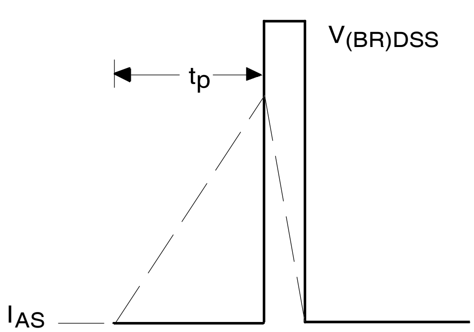


Fig 13b. Unclamped Inductive Waveforms

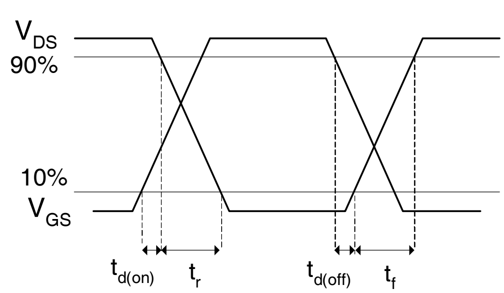
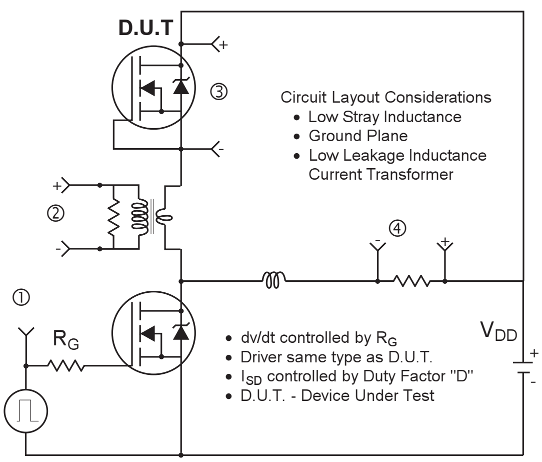
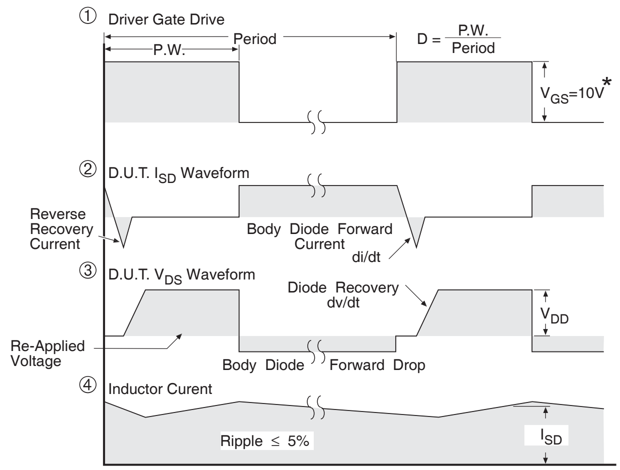


Fig 14b. Switching Time Waveforms





* V_{GS} = 5V for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

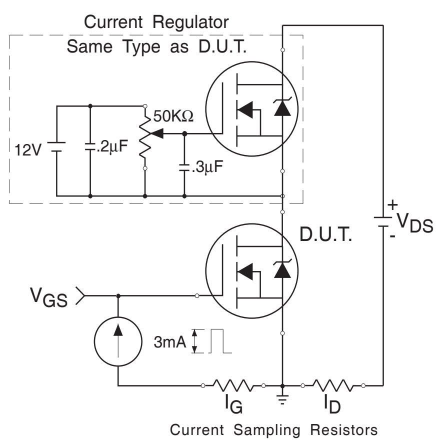


Fig 16. Gate Charge Test Circuit

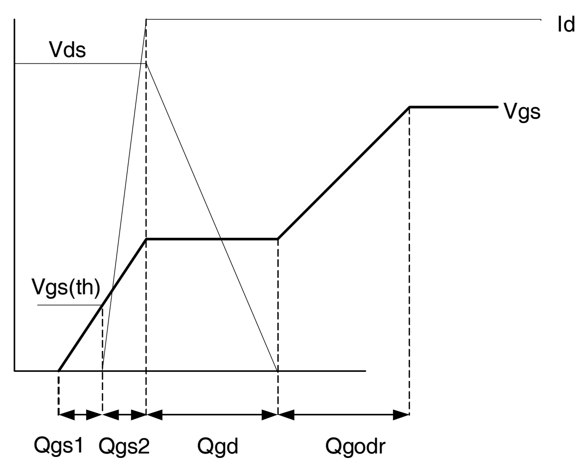
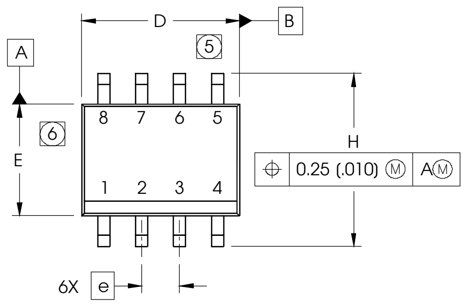


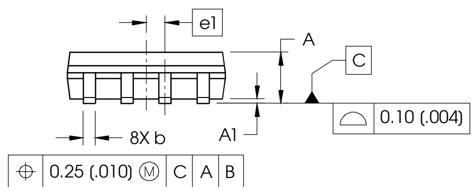
Fig 17. Gate Charge Waveform

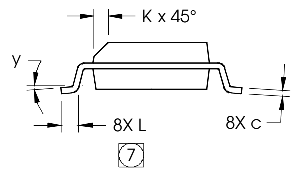
SO-8 Package Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°





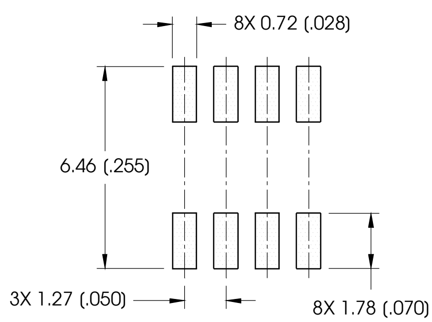
NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].

6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].

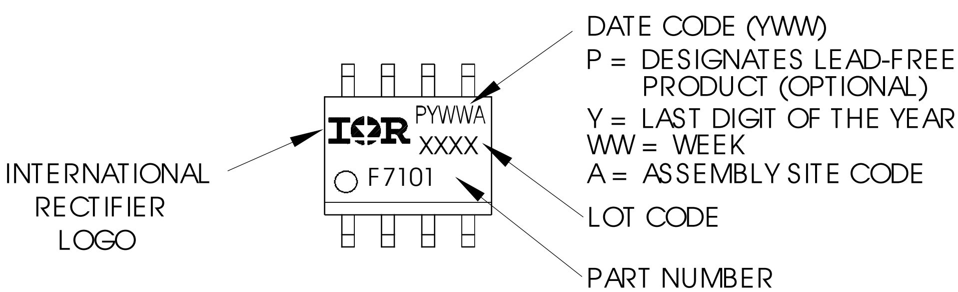
7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

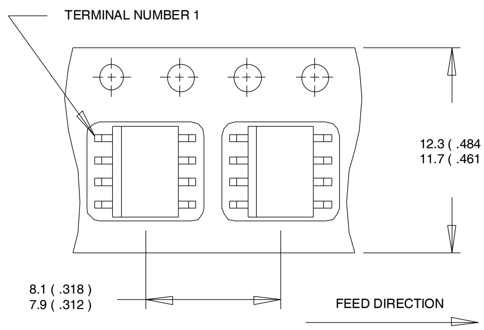
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



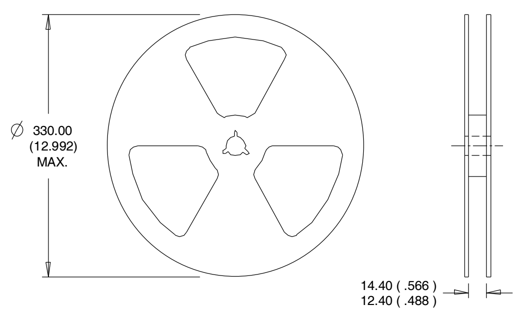
Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

Qualification information†

Qualification level	Consumer (per JEDEC JESD47F†† guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D††)
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability

†† Applicable version of JEDEC standard at the time of product release

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting $T_J = 25°C$, $L = 0.5mH$ $R_G = 25\Omega$, $I_{AS} = 14A$.

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④ When mounted on 1 inch square copper board

⑤ R_θ is measured at T_J approximately 90°C

Revision History

Date	Comment
7/8/2014	• Updated data sheet based on corporate template. • Added Qual level on page10. • Added ordering information on page1 • Updated Max RG from "TBD" to "2.6Ohm" on page2.

International Rectifier

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